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TC 1700

Docket No.: 8733.154.00-US
(PATENT)

Handwritten: 4/18/03
Signature: [illegible]

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Jin Jang, et al

Application No.: 09/350,313

Group Art Unit: 1765

Filed: July 9, 1999

Examiner: R. Kunemund

For: METHOD OF CRYSTALLIZING
AMORPHOUS SILICON LAYER AND
CRYSTALLIZING APPARATUS THEREOF

AMENDMENT AFTER RCE

Box RCE
Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated December 16, 2002 (Paper No. 22), finally rejecting claims 1-19, 22, and 24-41 please amend the above-identified U.S. patent application as follows:

In the Claims

Please cancel claims 14 and 15 without prejudice or disclaimer.

Please amend the claims as follows (A marked-up copy of the amended claims is attached):

1. (Amended) A method of crystallizing amorphous silicon, comprising:
- depositing an inducing substance for silicon crystallization on an exposed surface of an amorphous silicon layer by plasma exposure; and
- annealing the amorphous silicon layer,

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